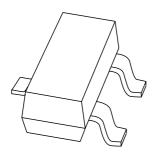
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBS3904 NPN general purpose transistor

Product specification Supersedes data of 1999 Apr 22 2004 Feb 02





NPN general purpose transistor

PMBS3904

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

 General purpose switching and amplification, e.g. telephony and professional communication equipment.

DESCRIPTION

NPN transistor in a plastic SOT23 package.

PNP complement: PMBS3906.

MARKING

TYPE NUMBER	MARKING CODE(1)
PMBS3904	*O4

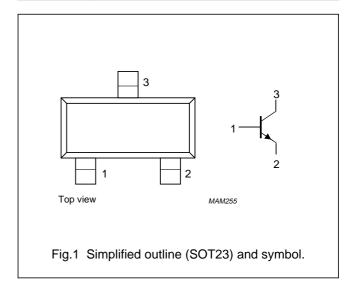
Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE		PACKAGE			
NUMBER	NAME	DESCRIPTION VERSION			
PMBS3904	_	plastic surface mounted package; 3 leads SOT23			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current capability		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

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NPN general purpose transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	50	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	_	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; note 1; (see Fig.2)			
		I _C = 0.1 mA	40	_	
		I _C = 1 mA	70	_	
		I _C = 10 mA	100	300	
		I _C = 50 mA	60	_	
		I _C = 100 mA	30	_	
V _{CEsat}	collector-emitter saturation	I _C = 10 mA; I _B = 1 mA	_	200	mV
	voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	_	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	650	850	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	_	950	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 5 \text{ V}$; $f = 1 \text{ MHz}$	_	4	pF
Ce	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 0.5 \text{ V}$; $f = 1 \text{ MHz}$	_	12	pF
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 20 \text{ V}; f = 100 \text{ MHz}$	180	_	MHz
F	noise figure	I_C = 100 μA; V_{CE} = 5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	_	5	dB
Switching t	imes (between 10% and 90% leve	els); (see Fig.3)			
t _{on}	turn-on time	I _{Con} = 10 mA; I _{Bon} = 1 mA;	_	110	ns
t _d	delay time	$I_{Boff} = -1 \text{ mA}; V_{CC} = 3 \text{ V};$	_	50	ns
t _r	rise time	$V_{BB} = -1.9 \text{ V}$	_	60	ns
t _{off}	turn-off time	1	_	1200	ns
t _s	storage time]	_	1000	ns
t _f	fall time]	_	200	ns

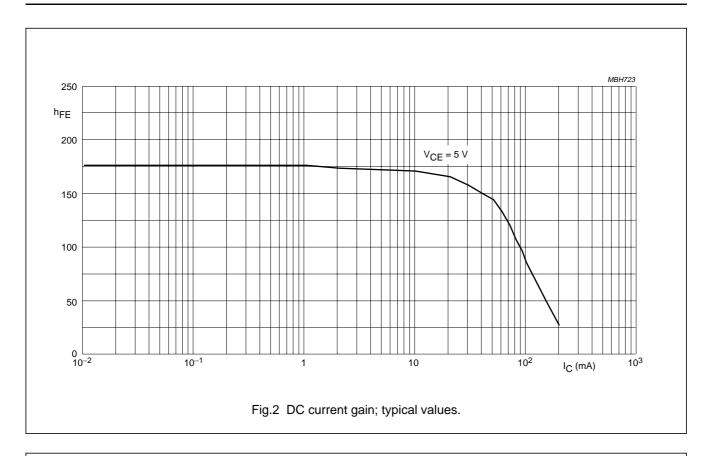
Note

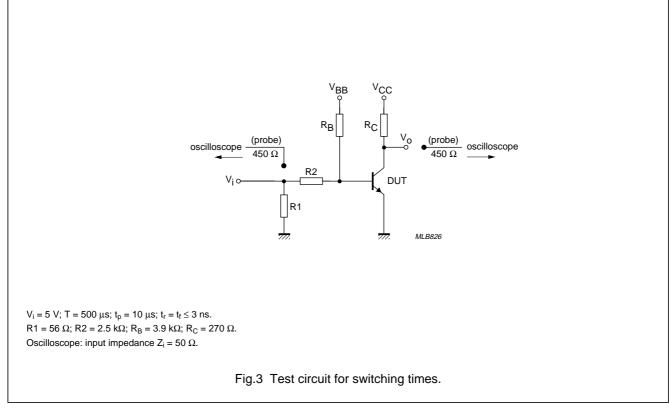
1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

Philips Semiconductors Product specification

NPN general purpose transistor

PMBS3904





Philips Semiconductors Product specification

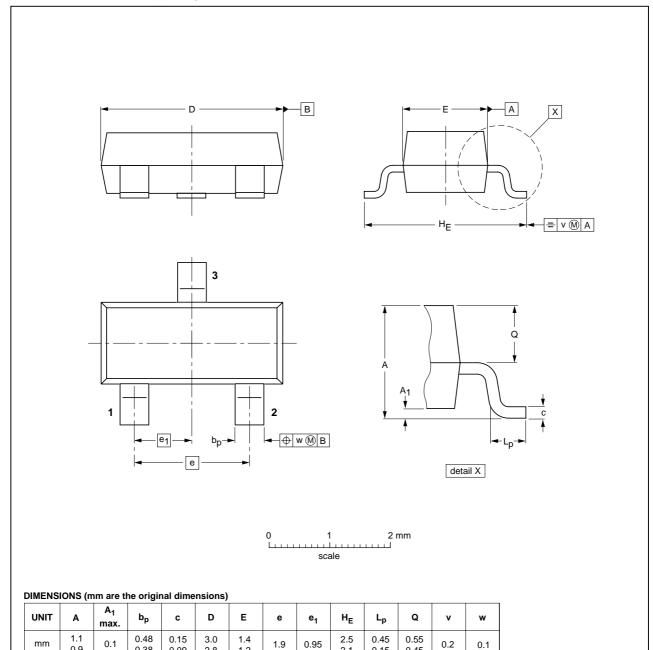
NPN general purpose transistor

PMBS3904

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC JEDEC EIAJ			PROJECTION	ISSUE DATE	
SOT23		TO-236AB				97-02-28 99-09-13

2004 Feb 02 5

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Philips Semiconductors Product specification

NPN general purpose transistor

PMBS3904

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Printed in The Netherlands

R75/05/pp7

Date of release: 2004 Feb 02

Document order number: 9397 750 12449

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